Switch-mode Power Rectifier

60 V, 30 A

MBR30L60CTG, MBRF30L60CTG

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 30 A Total (15 A Per Diode Leg)
- Guard−Ring for Stress Protection
- These Devices are Pb−Free and are RoHS Compliant

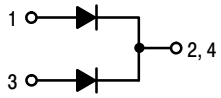
Applications

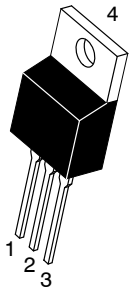
- Power Supply − Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO−220 & TO−220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

SCHOTTKY BARRIER RECTIFIER
30 AMPERES, 60 VOLTS

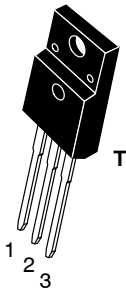




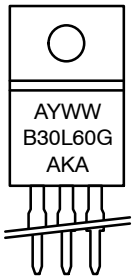
TO−220
CASE 221A
STYLE 6

MARKING DIAGRAMS





TO−220 FULLPAK™
CASE 221D



A	= Assembly Location
Y	= Year
WW	= Work Week
B30L60	= Device Code
G	= Pb−Free Device
AKA	= Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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MAXIMUM RATINGS (Per Diode Leg)

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V_{RRM} V_{RWM} V_R	60	V
Average Rectified Forward Current MBR30L60CTG (Rated V_R) T_C = 133°C MBRF30L60CTG (Rated V_R) T_C = 108°C	(Per Leg) (Per Device) (Per Device)	$I_{F(AV)}$	15 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	240	A
Operating Junction Temperature (Note 1)		T_J	−55 to +150	°C
Storage Temperature		T_{stg}	−65 to +175	°C
ESD Ratings:	Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic		Symbol	Value	Unit
Maximum Thermal Resistance				°C/W
MBR30L60CTG	Junction−to−Case	$R_{\theta JC}$	2.1	
	Junction−to−Ambient	$R_{\theta JA}$	70	
MBRF30L60CTG	Junction−to−Case	$R_{\theta JC}$	5.0	
	Junction−to−Ambient	$R_{\theta JA}$	75	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2)	v_F			V
(I_F = 15 A, T_C = 25°C)		0.57	0.62	
(I_F = 15 A, T_C = 125°C)		0.53	0.57	
(I_F = 30 A, T_C = 25°C)		0.75	0.81	
(I_F = 30 A, T_C = 125°C)		0.70	0.73	
Maximum Instantaneous Reverse Current (Note 2)	i_R			
(Rated DC Voltage, T_C = 25°C)		137	350	μA
(Rated DC Voltage, T_C = 125°C)		62	110	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MBR30L60CTG	TO−220 (Pb−Free)	50 Units / Rail
MBRF30L60CTG	TO−220FP (Pb−Free)	50 Units / Rail

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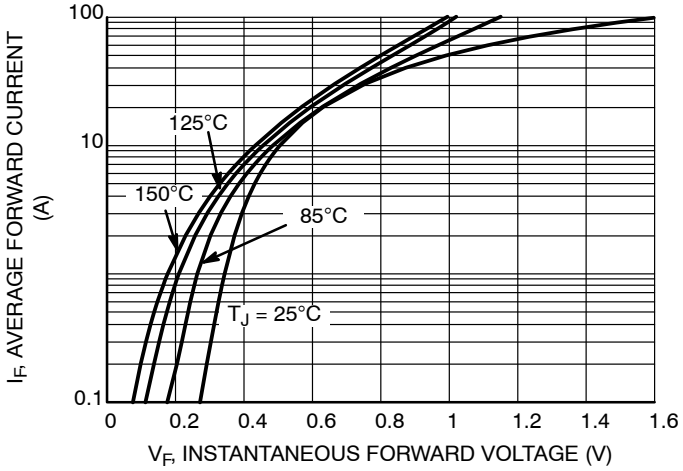


Figure 1. Typical Forward Voltage

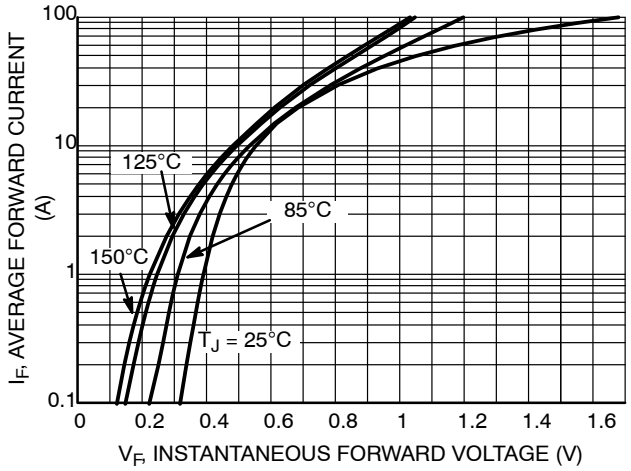


Figure 2. Maximum Forward Voltage

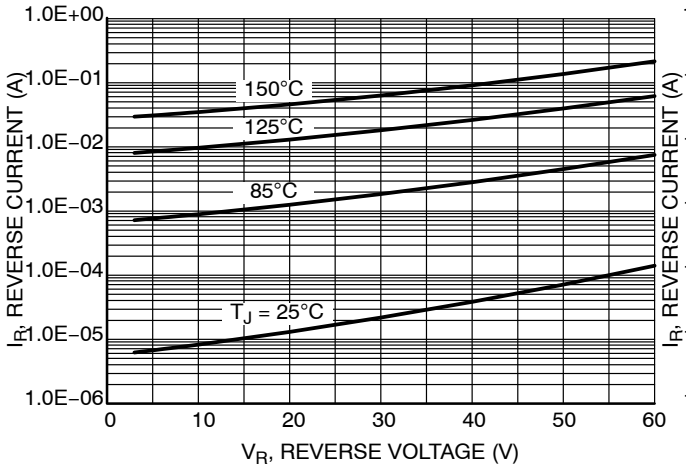


Figure 3. Typical Reverse Current

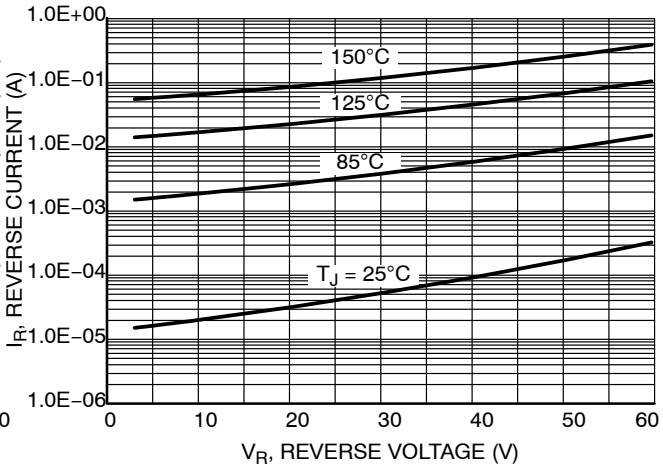


Figure 4. Maximum Reverse Current

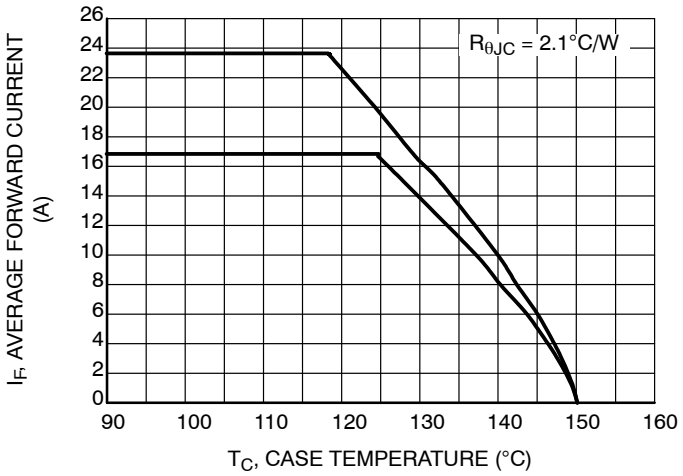


Figure 5. Current Derating, Case per Leg
MBR30L60CT

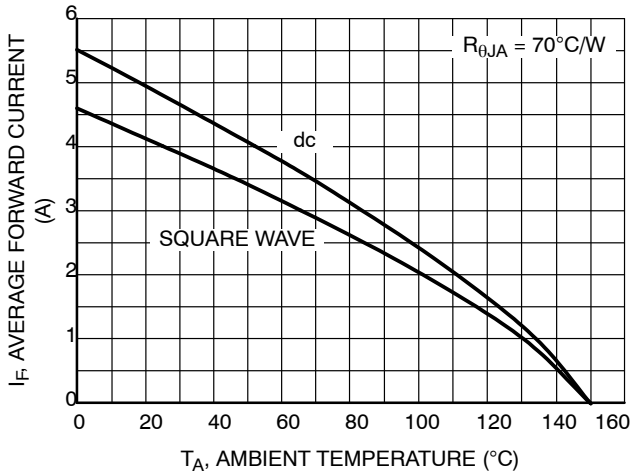


Figure 6. Current Derating, Ambient per Leg
MBR30L60CT

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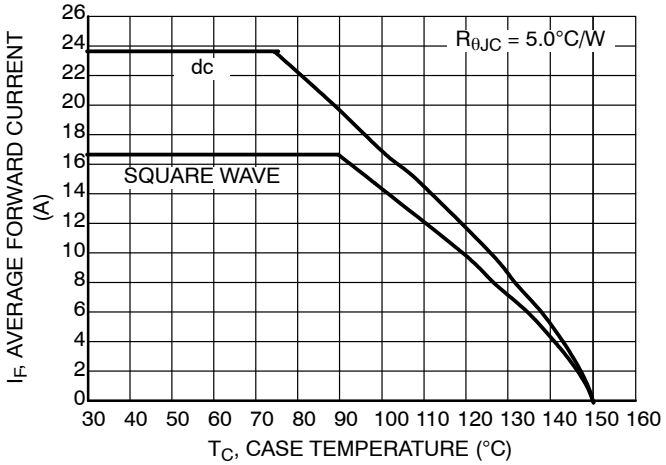


Figure 7. Current Derating, Case per Leg MBRF30L60CT

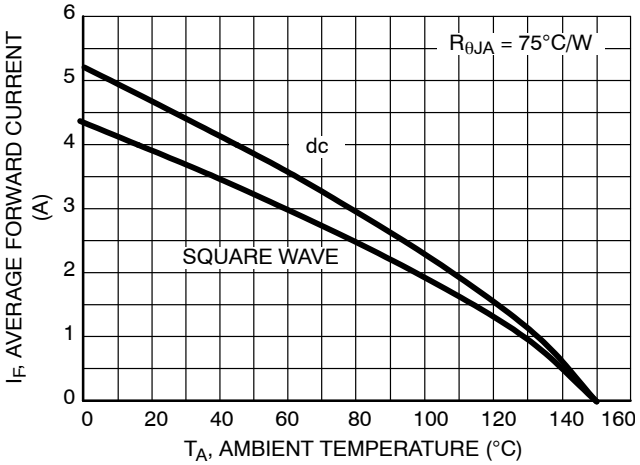


Figure 8. Current Derating, Ambient per Leg MBRF30L60CT

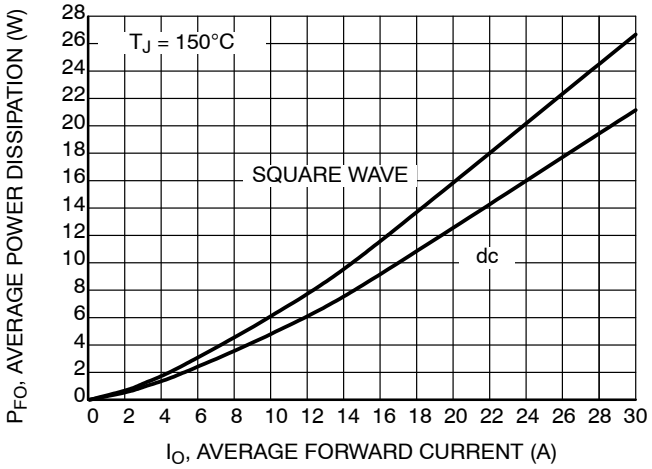


Figure 9. Forward Power Dissipation

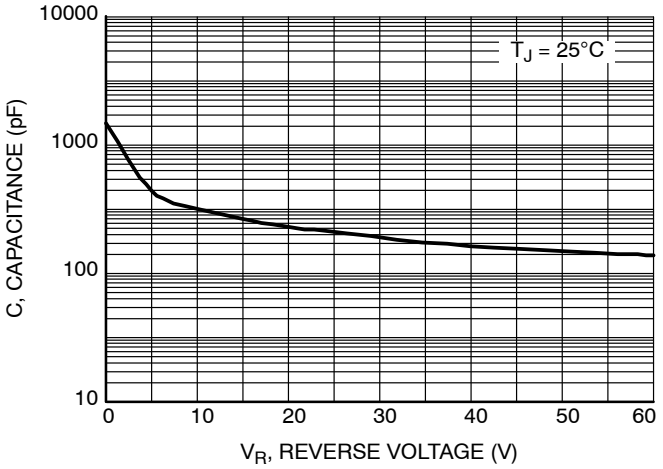


Figure 10. Capacitance

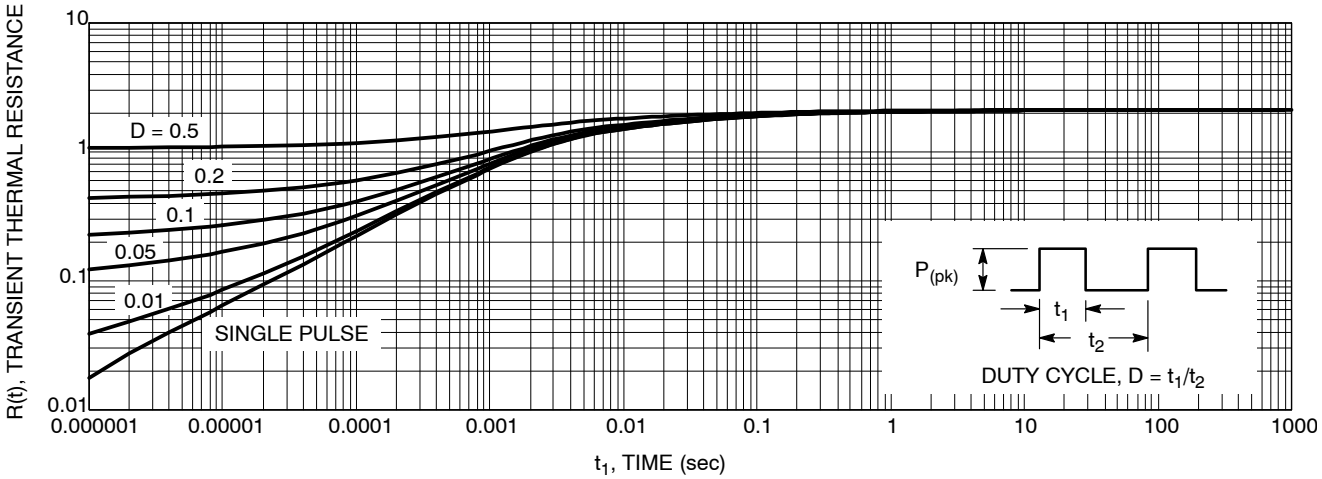


Figure 11. Thermal Response Junction−to−Case, per Leg for MBR30L60CT

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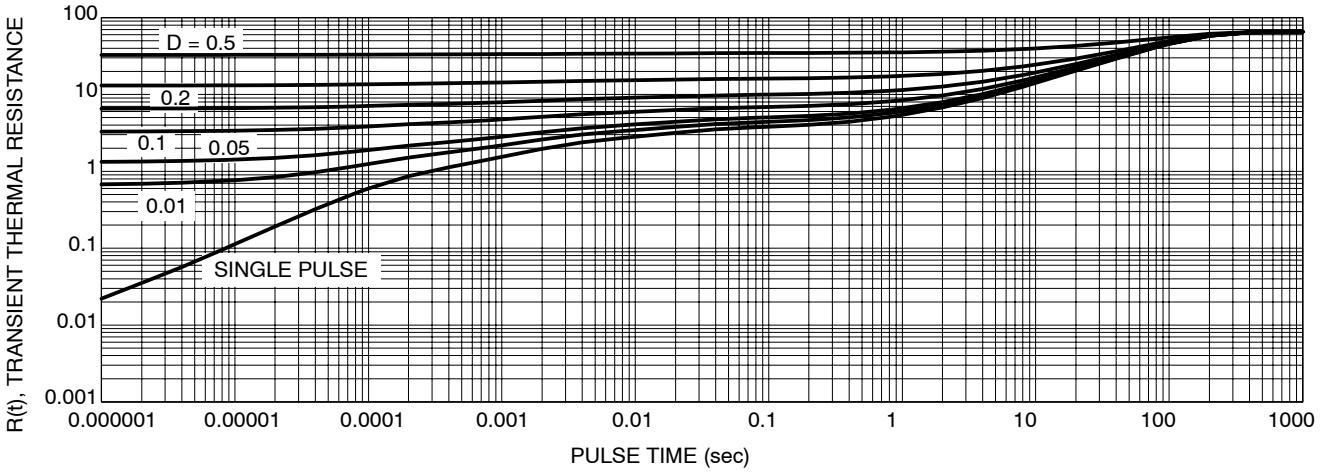


Figure 12. Thermal Response Junction−to−Ambient, per Leg for MBR30L60CT

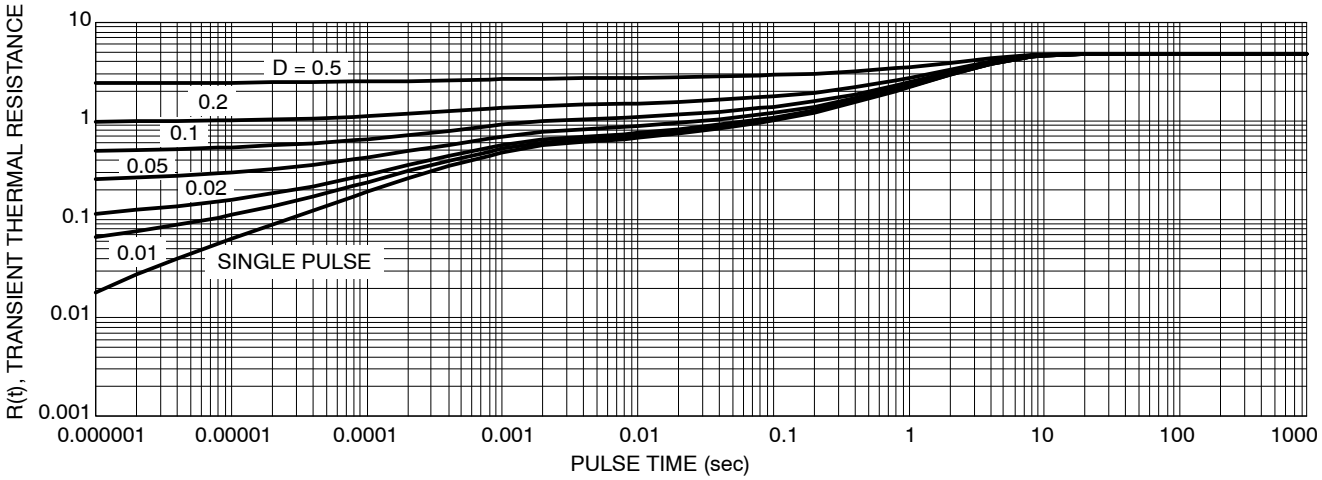


Figure 13. Thermal Response Junction−to−Case, per Leg for MBRF30L60CT

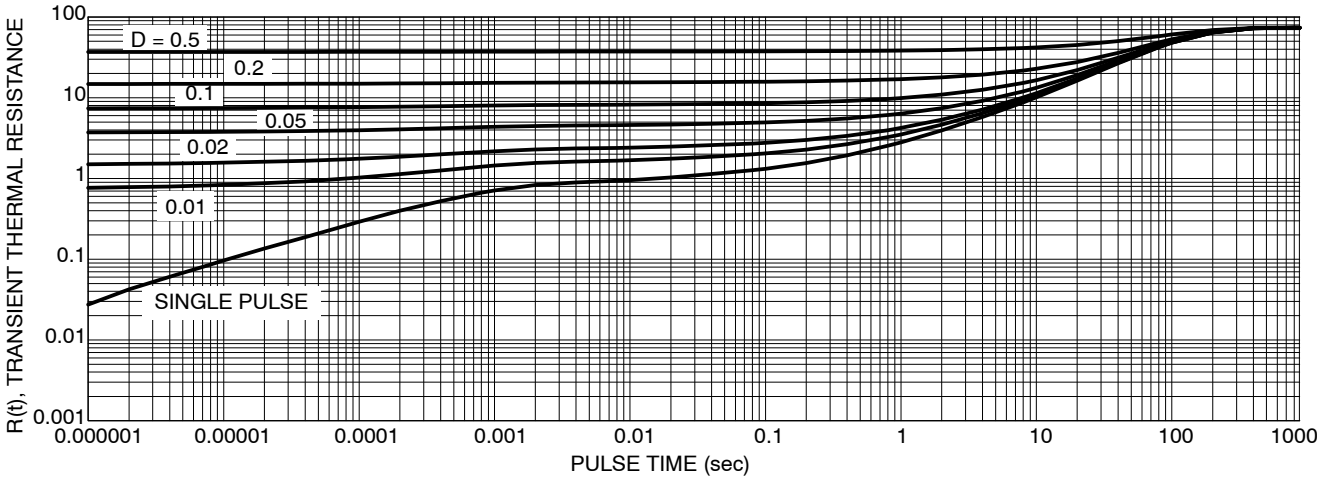


Figure 14. Thermal Response Junction−to−Ambient, per Leg for MBRF30L60CT

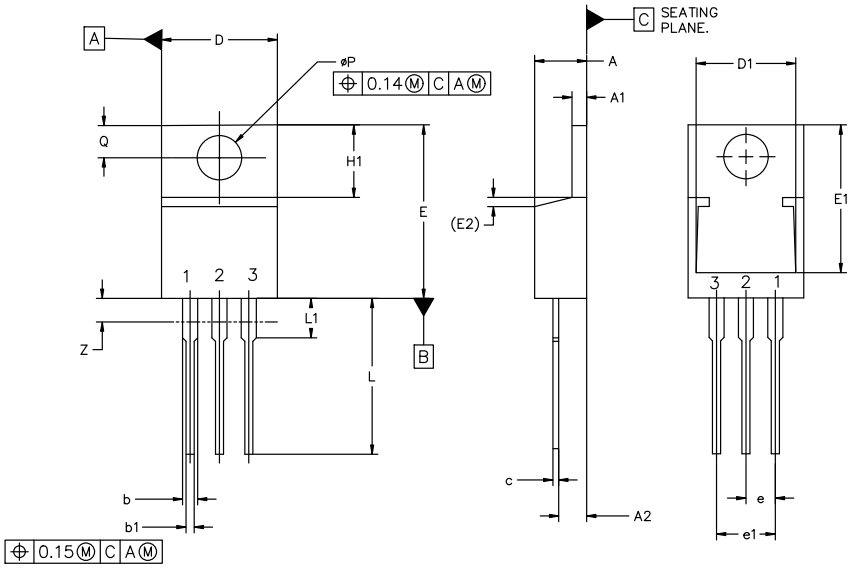
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TO−220−3 10.10x15.12x4.45, 2.54P
CASE 221A
ISSUE AL

DATE 05 FEB 2025



MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
øP	3.60	3.85	4.09
Z	−.−−	−.−−	3.48

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

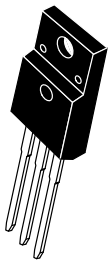
STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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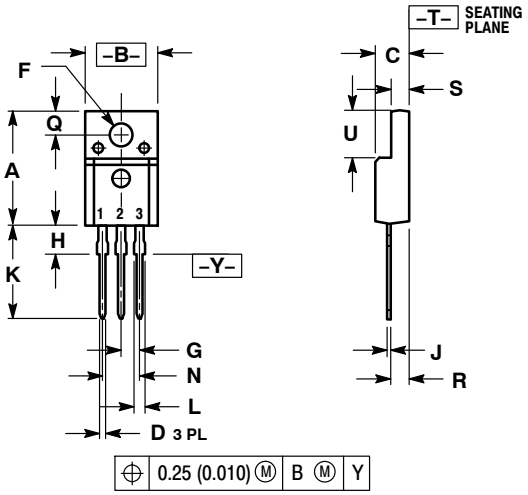
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SCALE 1:1

TO−220 FULLPAK
CASE 221D−03
ISSUE K

DATE 27 FEB 2009



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH
3. 221D−01 THRU 221D−02 OBSOLETE, NEW STANDARD 221D−03.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 2:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

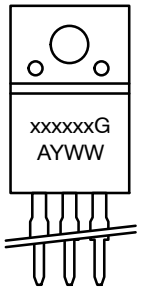
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2. CATHODE
3. ANODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. CATHODE

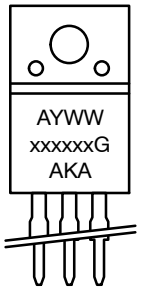
STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 6:
PIN 1. MT 1
2. MT 2
3. GATE

MARKING DIAGRAMS



Bipolar



Rectifier

xxxxxx	= Specific Device Code
G	= Pb−Free Package
A	= Assembly Location
Y	= Year
WW	= Work Week

A	= Assembly Location
Y	= Year
WW	= Work Week
xxxxxx	= Device Code
G	= Pb−Free Package
AKA	= Polarity Designator

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